

KS54AHCT 374

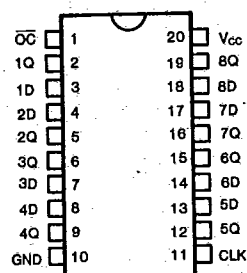
KS74AHCT

Octal D-Type Flip-Flops with 3-State Outputs

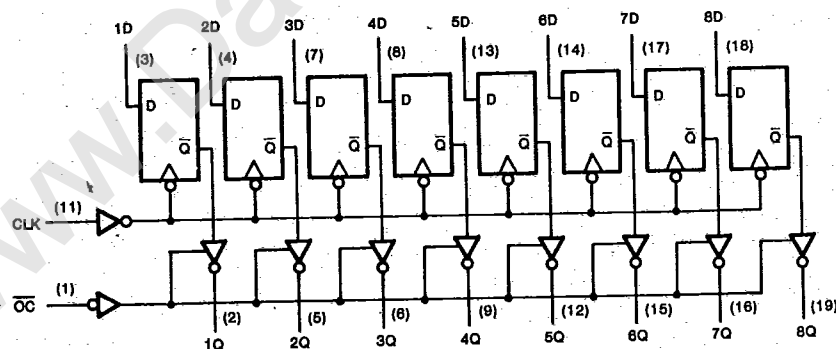
FEATURES

- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- 3-State outputs with high drive current ($I_{OL} = 24 \text{ mA}$ @ $V_{OL} = 0.5\text{V}$) for direct bus interface
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:
KS74AHCT: -40°C to $+85^\circ\text{C}$
KS54AHCT: -55°C to $+125^\circ\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

PIN CONFIGURATION



LOGIC DIAGRAM



DESCRIPTION

The '374 consists of 8 high-speed D-type edge-triggered flip-flops coupled to 3-state output buffers with high drive current capability. It can be used in implementing buffer registers, I/O ports, bidirectional bus driver and working registers.

The flip-flops are edge-triggered on the positive transition of the clock. The Q outputs are set to the logic levels that were set up at the D inputs.

The output buffers are controlled by a common signal ($\overline{OC}$) which places the outputs at a high-impedance state when it is taken high. The OC signal does not affect the internal operations of the flip-flops. Old data can be retained or new data can be entered while outputs are off.

These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

FUNCTION TABLE

(Each Flip-Flop)

Inputs			Output
$\overline{OC}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	L	X	Q_0
H	X	X	Z



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KS54AHCT
KS74AHCT
374
Octal D-Type Flip-Flops
with 3-State Outputs
T-46-07-05
Absolute Maximum Ratings*

Supply Voltage Range V_{CC} , -0.5V to +7V
 DC Input Diode Current, I_{IK}
 ($V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$) ± 20 mA
 DC Output Diode Current, I_{OK}
 ($V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$) ± 20 mA
 Continuous Output Current Per Pin, I_O
 ($-0.5V < V_O < V_{CC} + 0.5V$) ± 70 mA
 Continuous Current Through
 V_{CC} or GND pins ± 250 mA
 Storage Temperature Range, T_{stg} , ... -65°C to +150°C
 Power Dissipation Per Package, P_d 500 mW

* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

Power Dissipation temperature derating:

Plastic Package (N): -12mW/°C from 65°C to 85°C

Ceramic Package (J): -12mW/°C from 100°C to 125°C

Recommended Operating Conditions

 Supply Voltage, V_{CC} 4.5V to 5.5V

 DC Input & Output Voltages*, V_{IN} , V_{OUT} ... 0V to V_{CC}

Operating Temperature

Range KS74AHCT: -40°C to +85°C

KS54AHCT: -55°C to +125°C

 Input Rise & Fall Times, t_r , t_f Max 500 ns

 * Unused inputs must always be tied to an appropriate logic voltage level (either V_{CC} or GND)

DC ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$ Unless Otherwise Specified)

Characteristic	Symbol	Test Conditions	T _a = 25°C		KS74AHCT	KS54AHCT	Unit
			Typ	Guaranteed Limits			
Minimum High-Level Input Voltage	V _{IH}			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V _{IL}			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V _{OH}	V _{IN} =V _{IH} or V _{IL} I _O = -20μA I _O = -6mA	V _{CC} 4.2	V _{CC} - 0.1 3.98	V _{CC} - 0.1 3.84	V _{CC} - 0.1 3.7	V
Maximum Low-Level Output Voltage	V _{OL}	V _{IN} =V _{IH} or V _{IL} I _O = 20μA I _O = 12mA I _O = 24mA	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	I _{IN}	V _{IN} =V _{CC} or GND		±0.1	±1.0	±1.0	μA
Maximum 3-State Leakage Current	I _{OZ}	Output Enable = V _{IH} V _{OUT} =V _{CC} or GND		±0.5	±5.0	±10.0	μA
Maximum Quiescent Supply Current	I _{CC}	V _{IN} =V _{CC} or GND I _{OUT} =0μA		8.0	80.0	160.0	μA
Additional Worst Case Supply Current	ΔI _{CC}	per input pin V _I =2.4V other Inputs: at V _{CC} or GND I _{OUT} =0μA		2.7	2.9	3.0	mA



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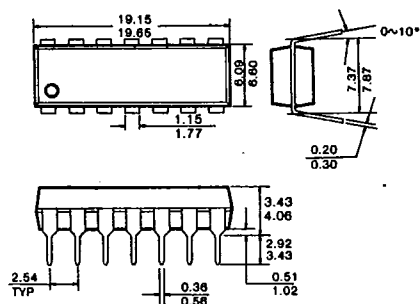
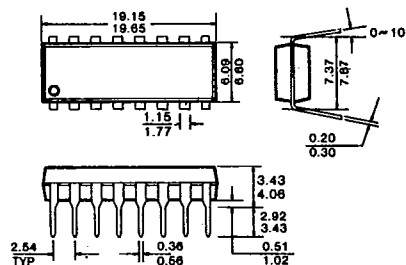
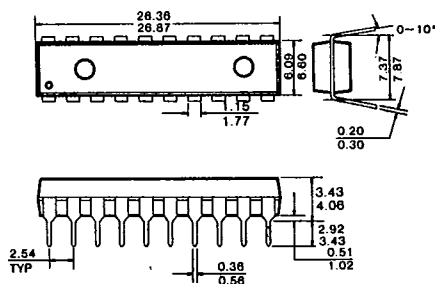
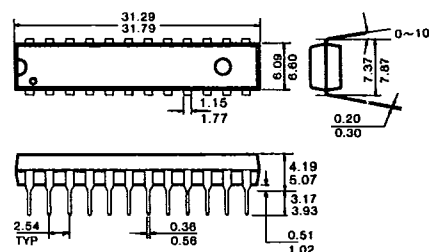
AC ELECTRICAL CHARACTERISTICS (Input $t_r, t_f \leq 2$ ns), AHCT374

Characteristic	Symbol	Conditions†		T _A = 25°C V _{CC} = 5.0V	KS74AHCT T _A = -40°C to +85°C V _{CC} = 5.0V ± 10%		KS54AHCT T _A = -55°C to +125°C V _{CC} = 5.0V ± 10%		Unit
				Typ	Min	Max	Min	Max	
Maximum Operating Frequency	f _{max}	C _L = 50pF		50	35		30		MHz
Propagation Delay, CLK to any Q	t _{PLH}	C _L = 50pF		8		14		17	ns
		C _L = 150pF		11		19		23	
	t _{PHL}	C _L = 50pF		8		14		17	
		C _L = 150pF		11		19		23	
Output Enable Time, OC to any Q	t _{PZH}	R _L = 1kΩ	C _L = 50pF	11		18		22	ns
			C _L = 150pF	14		23		28	
	t _{PZL}		C _L = 50pF	11		18		22	
			C _L = 150pF	14		23		28	
Output Disable Time, OC to any Q	t _{PHZ}	R _L = 1kΩ		13		18		22	ns
	t _{PLZ}	C _L = 50pF		13		18		22	
Pulse Width, CLK High or Low	t _w			7	15		18		ns
Setup Time, D before CLK†	t _{su}			9	14		13		ns
Hold Time, D after CLK†	t _h			-3	0		0		ns
Input Capacitance	C _{IN}			5					pF
Output Capacitance	C _{OUT}	Output Disabled		10					pF
Power Dissipation Capacitance*		OC = V _{CC}		5					
		OC = GND (per stage)		30					

* C_{PD} determines the no-load dynamic power dissipation: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

† For AC switching test circuits and timing waveforms see section 2.



PACKAGE DIMENSIONS*T-90-20***1. PLASTIC PACKAGES****14-Pin Plastic DIP Units: mm****16-Pin Plastic DIP Units: mm****20-Pin Plastic DIP Units: mm****24-Pin Plastic DIP Units: mm**

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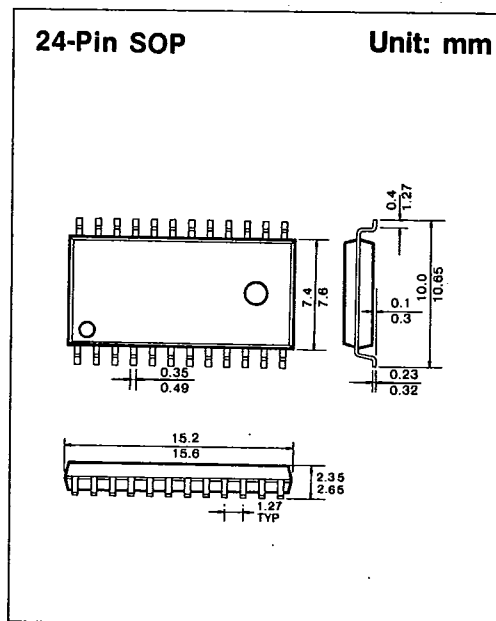
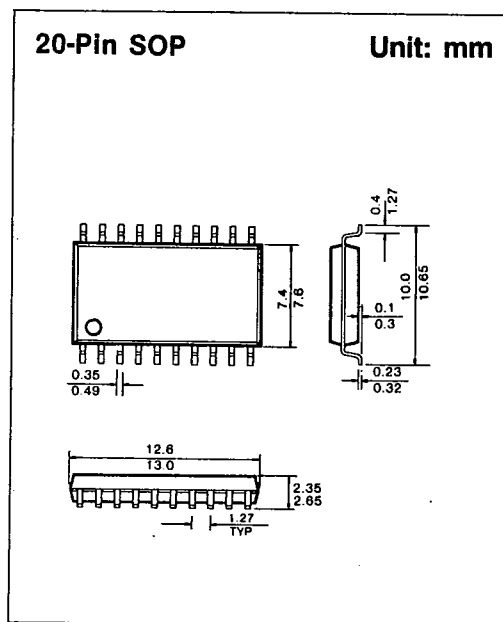
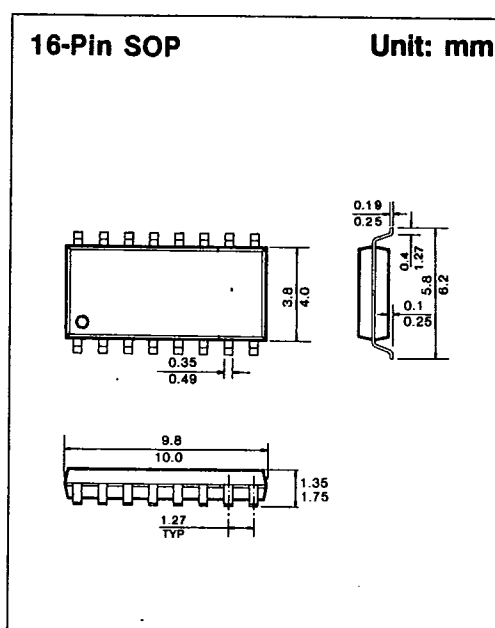
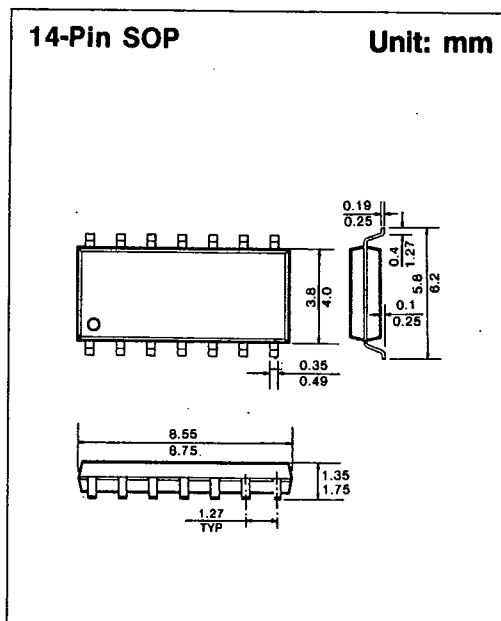
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PACKAGE DIMENSIONS

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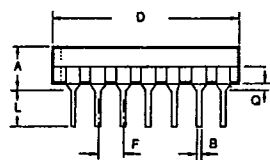
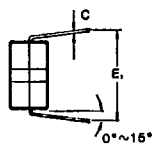
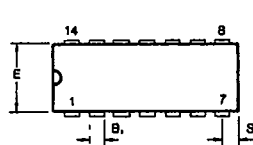
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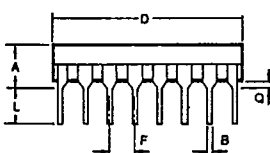
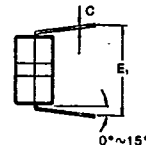
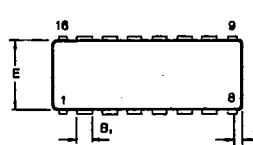
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PACKAGE DIMENSIONS

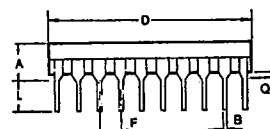
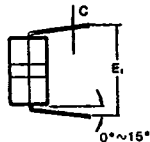
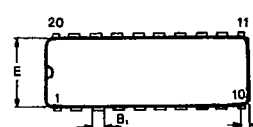
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2. CERAMIC PACKAGES**14-Pin Ceramic DIP Units: mm**

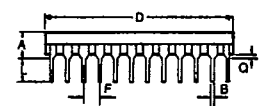
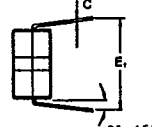
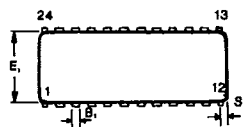
Dim	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	18.16	19.56
E	8.10	7.49
E ₁	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	1.91	2.29

16-Pin Ceramic DIP Units: mm

Dim	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	19.05	19.94
E	8.10	7.49
E ₁	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	0.51	1.14

20-Pin Ceramic DIP Units: mm

Dim	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	25.78	26.93
E	8.10	8.60
E ₁	7.77	7.98
F	2.54	
L	3.73	4.01
Q	0.38	0.89
S	0.51	1.14

24-Pin Ceramic DIP Units: mm

Dim	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	31.50	32.84
E	7.24	7.75
E ₁	7.77	7.98
F	2.54	
L	3.73	4.01
Q	0.508	1.778
S	1.85	1.93

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